SII O

S-57B1 Series

www.sii-ic.com

HIGH-SPEED UNIPOLAR DETECTION TYPE HALL IC

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Rev.1.0_00

The S-57B1 Series, developed by CMOS technology, is a high-accuracy Hall IC that operates with a high-sensitivity, a high-speed detection and low current consumption.

The output voltage changes when the S-57B1 Series detects the intensity level of flux density. Using the S-57B1 Series with a magnet makes it possible to detect the open / close and rotation state in various devices.

High-density mounting is possible by using the small SOT-23-3 package.

Due to its high-accuracy magnetic characteristics, the S-57B1 Series can make operation's dispersion in the system combined with magnet smaller.

Caution This product is intended to use in general electronic devices such as consumer electronics, office equipment, and communications devices. Before using the product in medical equipment or automobile equipment including car audio, keyless entry and engine control unit, contact to SII is indispensable.

■ Features

Pole detection:
 Detection of south pole
 Detection logic for magnetism*1:
 Active "L", active "H"

Output form*1: Nch open drain output, CMOS output

• Magnetic sensitivity: $B_{OP} = 3.0 \text{ mT typ.}$ • Operating cycle (current consumption): $50 \mu s (1400 \mu A) \text{ typ.}$ • Power supply voltage range: 2.7 V to 5.5 V• Operation temperature range: Ta = -40 °C to +125 °C

• Lead-free (Sn 100%), halogen-free*2

*1. The Option can be selected.

*2. Refer to "■ Product Name Structure" for details.

■ Applications

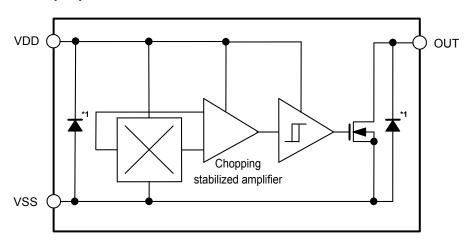
- Motor
- Housing equipment
- Industrial equipment

Package

• SOT-23-3

■ Block Diagrams

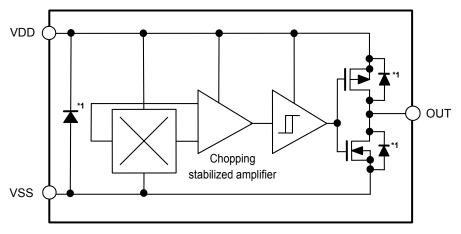
1. Nch open drain output product



*1. Parasitic diode

Figure 1

2. CMOS output product

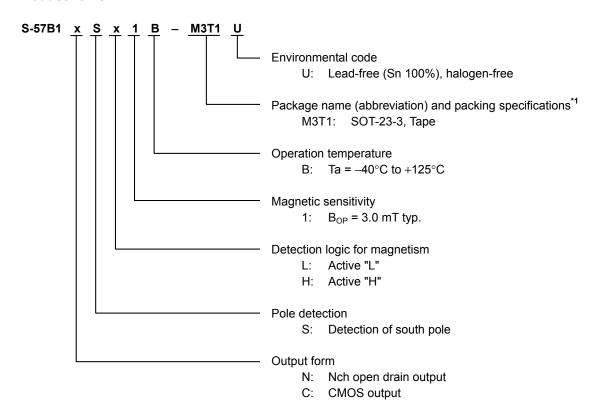


*1. Parasitic diode

Figure 2

■ Product Name Structure

1. Product name



^{*1.} Refer to the tape drawing.

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel
SOT-23-3	MP003-C-P-SD	MP003-C-C-SD	MP003-Z-R-SD

3. Product name list

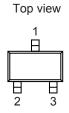
Table 2

Product Name	Output Form	Pole Detection	Detection Logic for Magnetism	Magnetic Sensitivity (B _{OP})	Operation temperature (Ta)
S-57B1NSL1B-M3T1U	Nch open drain output	South pole	Active "L"	3.0 mT typ.	-40°C to +125°C

Remark Please contact our sales office for products other than the above.

■ Pin Configuration

1. SOT-23-3



Pin No. Symbol Description

1 VSS GND pin

2 VDD Power supply pin

3 OUT Output pin

Table 3

Figure 3

■ Absolute Maximum Ratings

Table 4

(Ta = $+25^{\circ}$ C unless otherwise specified)

	Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltage	je	V_{DD}	$V_{SS} - 0.3$ to $V_{SS} + 7.0$	V
Output current		I _{OUT}	±2.0	mA
Output voltage	Nch open drain output product	V _{OUT}	V_{SS} – 0.3 to V_{SS} + 7.0	V
	CMOS output product		$V_{SS}-0.3$ to $V_{DD}+0.3$	V
Power dissipation		P _D	430 ^{*1}	mW
Operating ambient temperature		T _{opr}	-40 to +125	°C
Storage temperature		T _{stg}	-40 to +150	°C

^{*1.} When mounted on board

[Mounted board]

(1) Board size: 114.3 mm \times 76.2 mm \times t1.6 mm (2) Name: JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Electrical Characteristics

Table 5

(Ta = +25°C, V_{DD} = 5.0 V, V_{SS} = 0 V unless otherwise specified)

			(a = 0 0, 1 DD 0 0 0	•, • 33				
Item	Symbol	Condition		Min.	Тур.	Max.	Unit	Test Circuit
Power supply voltage	V_{DD}		_	2.7	5.0	5.5	V	_
Current consumption	I_{DD}	Average value		_	1400	2000	μΑ	1
Output voltage V _{OUT}		Nch open drain output product	Output transistor Nch, I _{OUT} = 2 mA	_	-	0.4	>	2
	V _{OUT}		Output transistor Nch, I _{OUT} = 2 mA	-	-	0.4	>	2
		CMOS output product	Output transistor Pch, $I_{OUT} = -2 \text{ mA}$	V _{DD} - 0.4	-	_	>	3
Leakage current	I _{LEAK}	Nch open drain output product Output transistor Nch, V _{OUT} = 5.5 V		-	_	1	μΑ	4
Operating cycle	t _{CYCLE}	-		_	50	100	μs	_

■ Magnetic Characteristics

Table 6

(Ta = $\pm 25^{\circ}$ C, V_{DD} = 5.0 V, V_{SS} = 0 V unless otherwise specified)

Item		Symbol	Condition	Min.	Тур.	Max.	Unit	Test Circuit
Operating point*1	South pole	B _{OPS}	_	1.4	3.0	4.0	mT	5
Release point*2	South pole	B _{RPS}	_	1.1	2.2	3.7	mT	5
Hysteresis width*3	South pole	B _{HYSS}	$B_{HYSS} = B_{OPS} - B_{RPS}$	ı	0.8	ı	mT	5

^{*1.} B_{OPS}: Operating point

The operating points are the values of magnetic flux density when the output voltage (V_{OUT}) is inverted after the magnetic flux density applied to the S-57B1 Series by the magnet (south pole) is increased (the magnet is moved closer).

Even when the magnetic flux density exceeds B_{OPS} , V_{OUT} retains the status.

*2. B_{RPS}: Release points

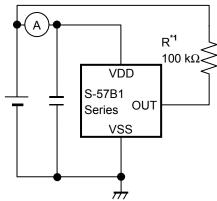
The release points are the values of magnetic flux density when the output voltage (V_{OUT}) is inverted after the magnetic flux density applied to the S-57B1 Series by the magnet (south pole) is decreased (the magnet is moved further away). Even when the magnetic flux density falls below B_{RPS} , V_{OUT} retains the status.

***3.** B_{HYSS}: Hysteresis widths

B_{HYSS} is the difference of magnetic flux density between B_{OPS} and B_{RPS}.

Remark The unit of magnetic density mT can be converted by using the formula 1 mT = 10 Gauss.

■ Test Circuits



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 4 Test Circuit 1

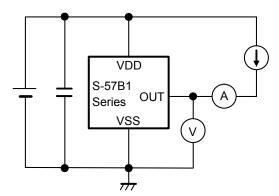


Figure 5 Test Circuit 2

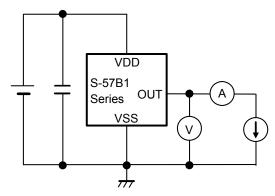


Figure 6 Test Circuit 3

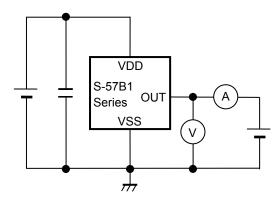
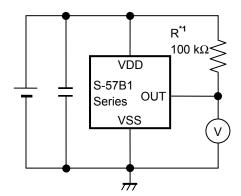


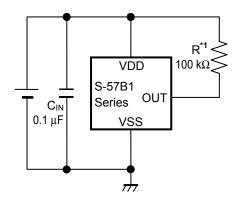
Figure 7 Test Circuit 4



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 8 Test Circuit 5

■ Standard Circuit



*1. Resistor (R) is unnecessary for the CMOS output product.

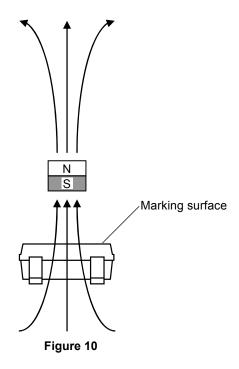
Figure 9

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

■ Operation

1. Direction of applied magnetic flux

The S-57B1 Series detects the magnetic flux density which is vertical to the marking surface. The output voltage (V_{OUT}) is inverted when the south pole is moved closer to the marking surface. **Figure 10** shows the direction in which magnetic flux is being applied.

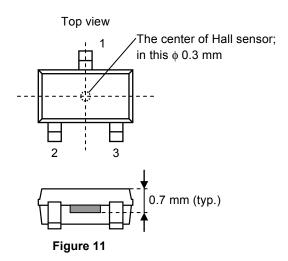


2. Position of Hall sensor

Figure 11 shows the position of Hall sensor.

The center of this Hall sensor is located in the area indicated by a circle, which is in the center of a package as described below.

The following also shows the distance (typ. value) between the marking surface and the chip surface of a package.



3. Basic operation

The S-57B1 Series changes the output voltage level (V_{OUT}) according to the level of the magnetic flux density (south pole) applied by a magnet.

The following explains the operation when the magnetism detection logic is active "L".

When the magnetic flux density vertical to the marking surface exceeds B_{OPS} after the south pole of a magnet is moved closer to the marking surface of the S-57B1 Series, V_{OUT} changes from "H" to "L". When the south pole of a magnet is moved further away from the marking surface of the S-57B1 Series and the magnetic flux density is lower than B_{RPS} , V_{OUT} changes from "L" to "H".

Figure 12 shows the relationship between the magnetic flux density and V_{OUT}.

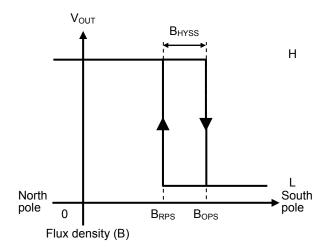


Figure 12

■ Precautions

- If the impedance of the power supply is high, the IC may malfunction due to a supply voltage drop caused by throughtype current. Take care with the pattern wiring to ensure that the impedance of the power supply is low.
- Note that the IC may malfunction if the power supply voltage rapidly changes.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Large stress on this IC may affect on the magnetic characteristics. Avoid large stress which is caused by bend and distortion during mounting the IC on a board or handle after mounting.
- SII claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ Marking Specification

1. SOT-23-3

Top view

1

(1) (2) (3) (4)

2

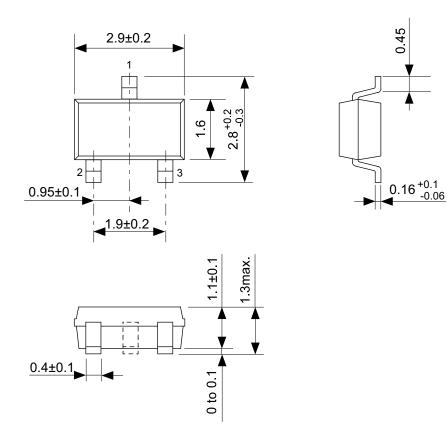
3

(1) to (3): Product code (Refer to **Product name vs. Product code**.)

(4): Lot number

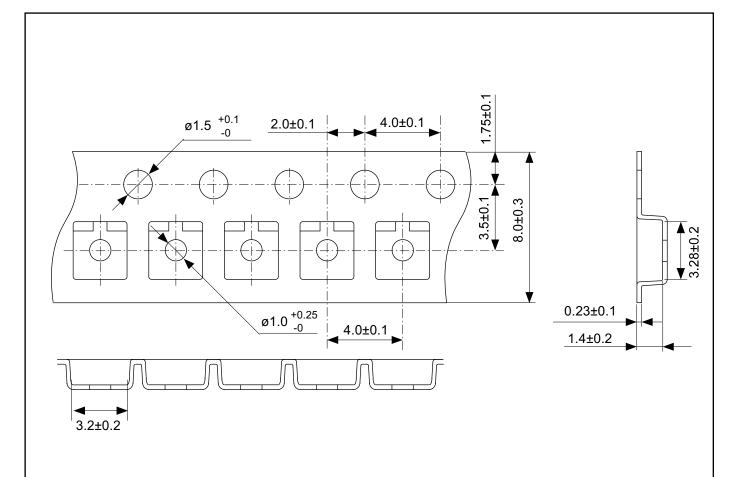
Product name vs. Product code

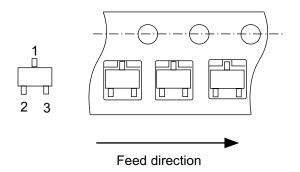
Product Name	Product Code			
i ioductivame	(1)	(2)	(3)	
S-57B1NSL1B-M3T1U	W	6	Α	



No. MP003-C-P-SD-1.0

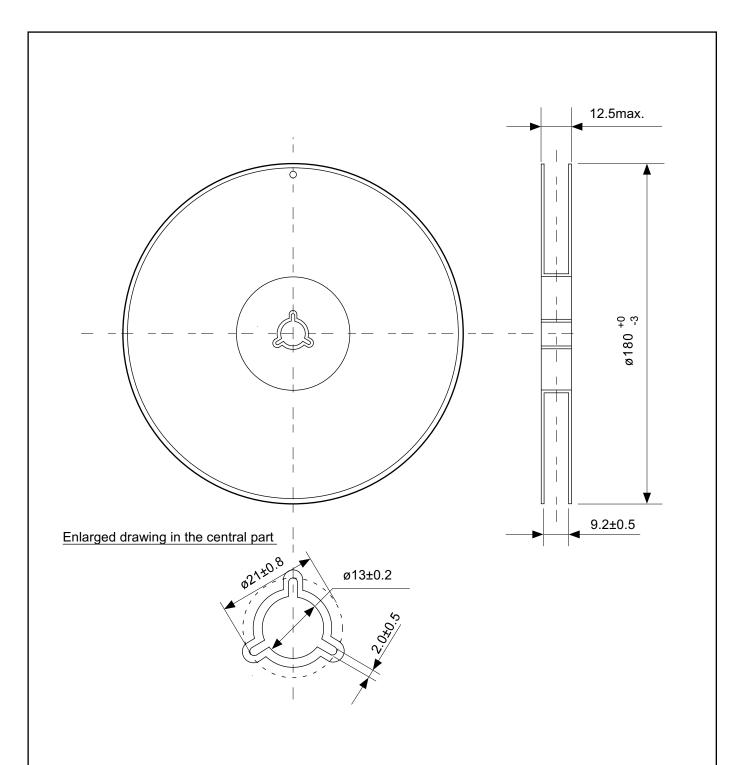
TITLE	SOT233-C-PKG Dimensions		
No.	MP003-C-P-SD-1.0		
SCALE			
UNIT	mm		
Seiko Instruments Inc.			





No. MP003-C-C-SD-2.0

SOT233-C-Carrier Tape			
MP003-C-C-SD-2.0			
mm			
Seiko Instruments Inc.			



No. MP003-Z-R-SD-1.0

TITLE	SOT233-C-Reel			
No.	MP00	3-Z-R-SD)-1.0	
SCALE		QTY.	3,000	
UNIT	mm			
Seiko Instruments Inc.				

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